

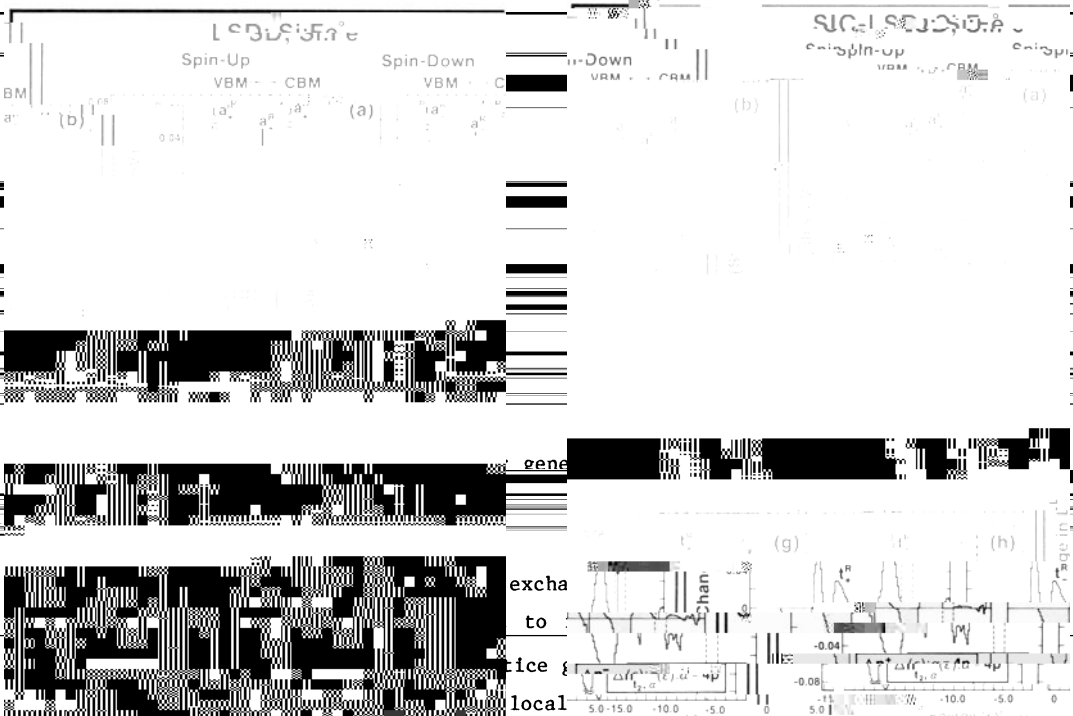
**HYPERFINE INTERACTION OF THE IRON IMPURITY NUCLEI AT THE
TETRAHEDRAL INTERSTITIAL SITE IN SILICON**

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Most electronic structure calculations on transition metal impurities in semiconductor¹⁻⁶ were performed within the local density formalism⁷, implemented either in an extended-crystal Green's function approach¹⁻², or within finite cluster models³⁻⁶. Involving a local (statistical) approximation to exchange and correlation, the local density approximation, much like its predecessor, the Thomas-Fermi model involves an unphysical interaction of each spin-orbital with itself⁸ (self-interaction). Whereas

significant effect on localized states. Such is the case for isolated transition atoms, where a self-interaction corrected model shows⁸ that relative to LSD (i) the 3d orbitals move to substantially more negative energies (increasing thereby the s-d separation), (ii) the 3d orbitals become more localized, whereas the non-d (valence)

in the self-consistent potential, we economize on the basis size using only the 1s-



the LSD formalism, and Fig. 1 (right) gives the corresponding results obtained in the LSD-SIC calculation. The major effects of SIC are seen to be: (i) a shift of all occupied pure d levels (i.e. e-representation) to more negative energies (e.g. e_+^b by 0.42 eV, and e_+^a by 0.33 eV), as they are relieved from the (repulsive) self-interaction, (ii) a corresponding upward shift of the occupied orbitals that contain substantial non-d character (e.g. the t_+^b , t_-^b and t_-^a move up by 0.09 eV, 0.4 eV and

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Note that whereas the LSD formalism emphasizes the difference between spin-up and

occupied and unoccupied orbitals. Hence, whereas the $e_+^a - e_-^a$ exchange splitting between the occupied e_+^a and unoccupied e_-^a gap levels of Si:Fe^0 is only 0.25 eV in LSD, it is three times larger in LSD-SIC, predominantly due to an upwards shift in e_-^a . This

upward shift of e_-^a has an important physical consequence. Whereas in the standard